

HiPerFRED™ Epitaxial Diode

ISOPLUS220™

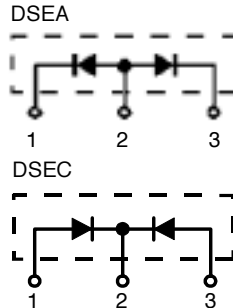
Electrically Isolated Back Surface

$$I_{FAV} = 2x21 \text{ A}$$

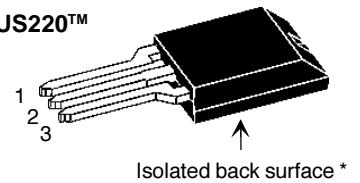
$$V_{RRM} = 600 \text{ V}$$

$$t_{rr} = 35 \text{ ns}$$

V_{RSM}	V_{RRM}	Type
V	V	
600	600	DSEA 59-06BC DSEC 59-06BC



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* Patent pending

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		60	A
I_{FAVM}	$T_C = 90^\circ\text{C}$; rectangular, $d = 0.5$	30	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	200	A
E_{AS}	$T_{VJ} = 25^\circ\text{C}$; non-repetitive $I_{AS} = 1.3 \text{ A}$; $L = 180 \mu\text{H}$	0.2	mJ
I_{AR}	$V_A = 1.5 \cdot V_R$ typical; $f = 10 \text{ kHz}$; repetitive	0.1	A
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	260	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	165	W
V_{ISOL}	50/60 Hz RMS; $I_{ISOL} \leq 1 \text{ mA}$	2500	V~
F_C	Mounting force	11...65 / 2.5...15	N / lb
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 150^\circ\text{C}$ $V_R = V_{RRM}$	200	μA
		2	mA
V_F ②	$I_F = 30 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$	1.75	V
		2.5	V
R_{thJC}		0.6	K/W
R_{thCH}			K/W
t_{rr}	$I_F = 1 \text{ A}$; $-di/dt = 200 \text{ A}/\mu\text{s}$; $V_R = 30 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$	30	ns
I_{RM}	$V_R = 100 \text{ V}$; $I_F = 50 \text{ A}$; $-di_F/dt = 100 \text{ A}/\mu\text{s}$ $T_{VJ} = 100^\circ\text{C}$	4	A

 Notes: Data given for $T_{VJ} = 25^\circ\text{C}$ and per diode unless otherwise specified

① Pulse test: pulse Width = 5 ms, Duty Cycle < 2.0 %

 ② Pulse test: pulse Width = 300 μs , Duty Cycle < 2.0 %

IXYS reserves the right to change limits, test conditions and dimensions.

Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- Low cathode to tab capacitance (<15pF)
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM} -values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

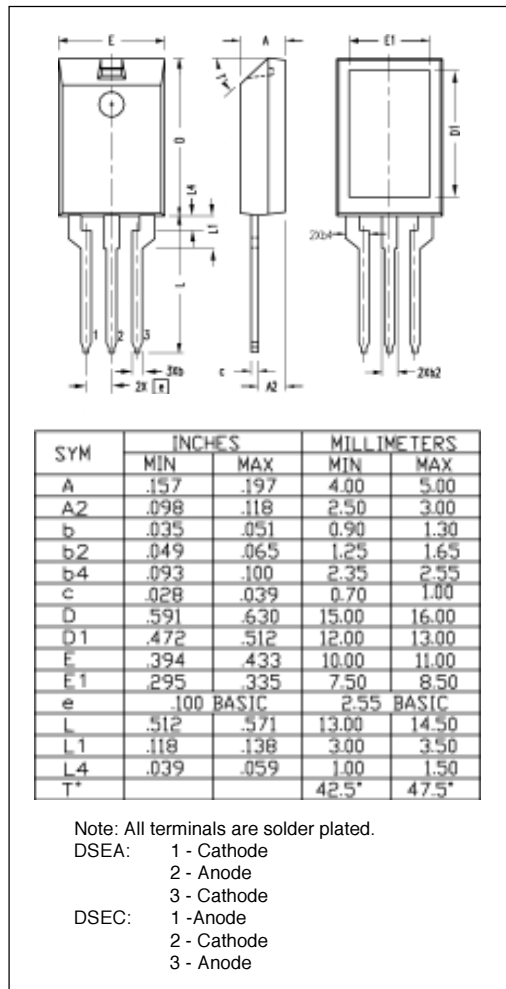
Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

ISOPLUS220 OUTLINE



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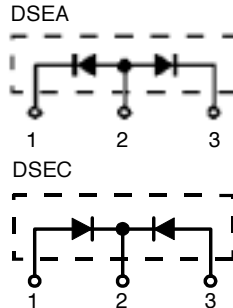
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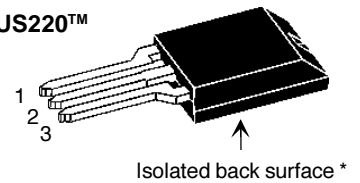
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R_{thJC} R_{thCH}		0.6	0.9 K/W K/W
t_{rr}	$I_F = 1 \text{ A}$; $-di/dt = 200 \text{ A}/\mu\text{s}$; $V_R = 30 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$	30	ns
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